PTO-1449

Application No. unknown

Applicant(s)
Scott R. Runnels

Information Disclosure Citation
in an Application

Docket Number
090936.0395

Group Art Unit unknown 212) Filing Date
October 24, 2000

## **U.S. PATENT DOCUMENTS**

		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
)U(	Α	5,655110	08/05/97	Krivokapic et al.	395	500	
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Bul	L	M. Bhusan et al. "Chemical-Mechanical Polishing in Semidirect Contact Mode", J. Electrochem. Soc., Vol. 142, No. 11, pp. 3845-3851	11/95
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EXAMINER

ALDERT W. PALADAN PATENT EXAMESER

considered. Include copy of this form with next communication to the applicant.

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not



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